

Silicon NPN Power Transistors

2SD1710

DESCRIPTION

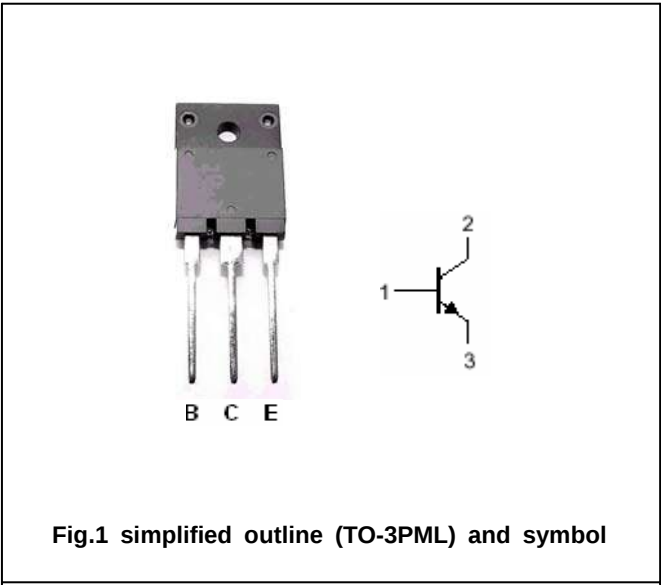
- With TO-3PML package
- High voltage;high speed
- High reliability.

APPLICATIONS

- Ultrahigh-definition CRT display
- Horizontal deflection output applications

PINNING

PIN	DESCRIPTION
1	Base
2	Collector
3	Emitter



Absolute maximum ratings(Ta=25℃)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V_{CBO}	Collector-base voltage	Open emitter	1500	V
V_{CEO}	Collector-emitter voltage	Open base	800	V
V_{EBO}	Emitter-base voltage	Open collector	6	V
I_C	Collector current		5	A
P_C	Collector power dissipation	$T_C=25^{\circ}C$	50	W
T_j	Junction temperature		150	℃
T_{stg}	Storage temperature		-55~150	℃

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CHARACTERISTICS

T_j=25°C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V _{CEQ(SUS)}	Collector-emitter sustaining voltage	I _C =100mA; I _B =0	800			V
V _{CEsat}	Collector-emitter saturation voltage	I _C =4.5A; I _B =2A			5.0	V
V _{BEsat}	Base-emitter saturation voltage	I _C =4.5A; I _B =2A			1.5	V
I _{EBO}	Emitter cut-off current	V _{EB} =4V; I _C =0			0.1	mA
I _{CBO}	Collector cut-off current	V _{CB} =800V; I _E =0			10	μ A
I _{CES}	Collector cut-off current	V _{CE} =1500V; R _{BE} =0			1.0	mA
h _{FE}	DC current gain	I _C =0.5 A ; V _{CE} =5V	10		40	

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PACKAGE OUTLINE

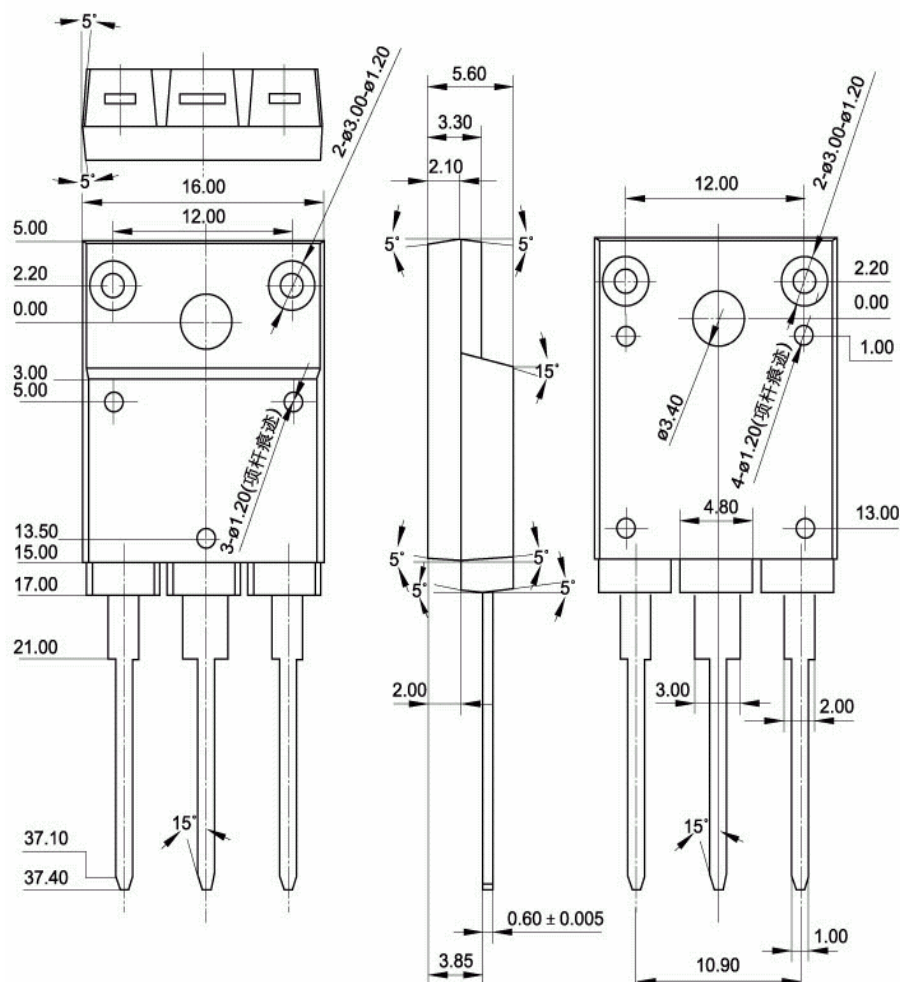


Fig.2 Outline dimensions